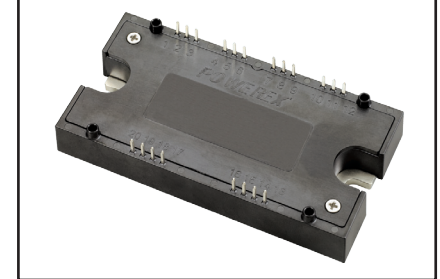
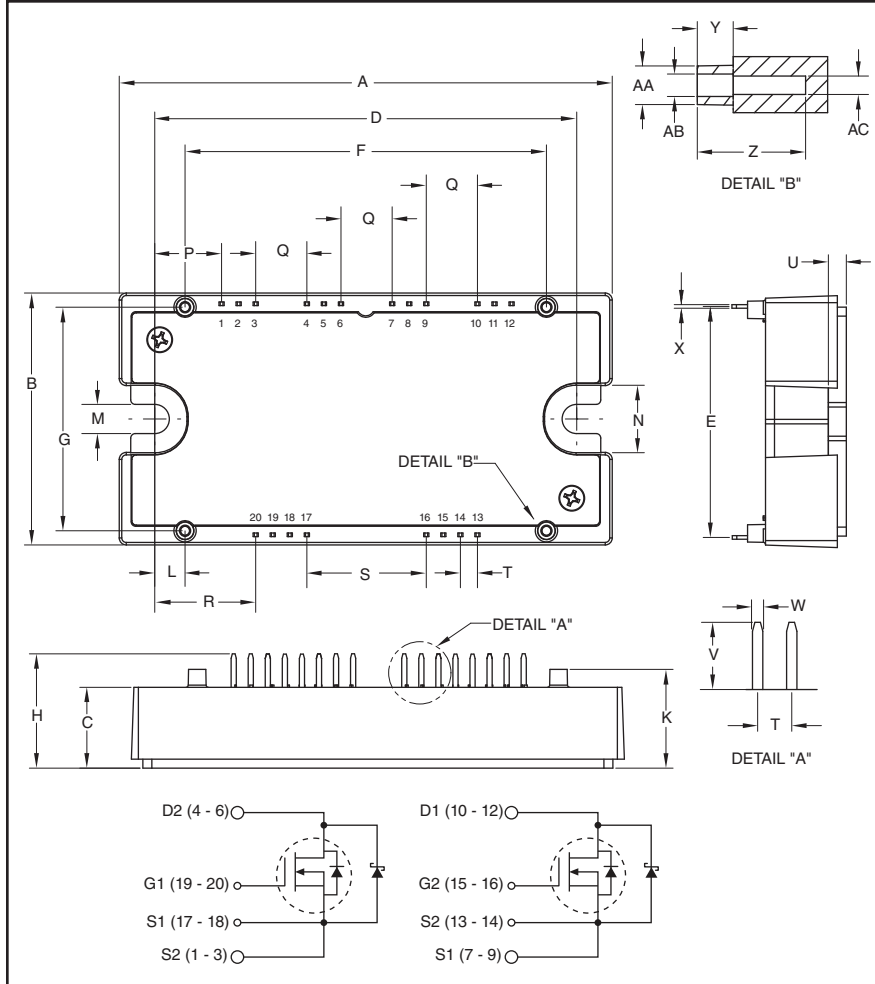


Split Dual SiC MOSFET Module 100 Amperes/1200 Volts



Description:

Powerex Silicon Carbide MOSFET Modules are designed for use in high frequency applications. Each module consists of two MOSFET Silicon Carbide Transistors with each transistor having a reverse connected fast recovery free-wheel silicon carbide Schottky diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Junction Temperature: 175°C
- Silicon Carbide Chips
- Low Internal Inductance
- Industry Leading RDS(on)
- High Speed Switching
- Low Switching Losses
- Low Capacitance
- Low Drive Requirement
- Fast 100A Free Wheeling Schottky Diode
- High Power Density
- Isolated Baseplate
- Aluminum Nitride Isolation
- 2 Individual Switches per Module
- AlSiC Baseplate

Applications:

- Energy Saving Power Systems such as:
Fans; Pumps; Consumer Appliances
- High Frequency Type Power Systems such as:
UPS; High Speed Motor Drives; Induction Heating; Welder; Robotics
- High Temperature Power Systems such as:
Power Electronics in Electric Vehicle and Aviation Systems

Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.32	109.8
B	2.21	56.1
C	0.71	18.0
D	3.70±0.02	94.0±0.5
E	2.026	51.46
F	3.17	80.5
G	1.96	49.8
H	1.00	25.5
K	0.87	22.0
L	0.266	6.75
M	0.26	6.5
N	0.59	15.0
P	0.586	14.89

Dimensions	Inches	Millimeters
Q	0.449	11.40
R	0.885	22.49
S	1.047	26.6
T	0.15	3.80
U	0.16	4.0
V	0.30	7.5
W	0.045	1.15
X	0.03	0.8
Y	0.16	4.0
Z	0.47	12.1
AA	0.17 Dia.	4.3 Dia.
AB	0.10 Dia.	2.5 Dia.
AC	0.08 Dia.	2.1 Dia.

QJD1210011
Split Dual SiC MOSFET Module
 100 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	QJD1210011	Units
Drain-Source Voltage (G-S Short)	V_{DSS}	1200	Volts
Gate-Source Voltage	V_{GSS}	-5 / +25	Volts
Drain Current (Continuous) at $T_C = 150^\circ\text{C}$	I_D	100	Amperes
Drain Current (Pulsed)*	$I_{D(\text{pulse})}$	250	Amperes
Maximum Power Dissipation ($T_C = 25^\circ\text{C}$, $T_j < 175^\circ\text{C}$)	P_D	900	Watts
Junction Temperature	T_j	-40 to 175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 150	$^\circ\text{C}$
Mounting Torque, M6 Mounting Screws	—	40	in-lb
Module Weight (Typical)	—	140	Grams
V Isolation Voltage	V_{RMS}	3000	Volts

MOSFET Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 50\mu\text{A}$, $V_{GS} = 0$	1200	—	—	Volts
Zero Gate Voltage Drain Current**	I_{DSS}	$V_{GS} = 0$, $V_{DS} = 1200\text{V}$	—	0.35	2.6	mA
Zero Gate Voltage Drain Current**	I_{DSS}	$V_{GS} = 0$, $V_{DS} = 1200\text{V}$, $T_j = 175^\circ\text{C}$	—	0.40	4.0	mA
Gate Leakage Current	I_{GSS}	$V_{DS} = 0$, $V_{GS} = 20\text{V}$	—	—	1.5	μA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 10\text{mA}$	1.5	2.5	5.0	Volts
		$V_{DS} = V_{GS}$, $I_D = 10\text{mA}$, $T_j = 175^\circ\text{C}$	1.0	1.7	5.0	Volts
Drain-Source On Resistance	$R_{DS(\text{on})}$	$I_D = 100\text{A}$, $V_{GS} = 20\text{V}$	—	15	25	$\text{m}\Omega$
		$I_D = 100\text{A}$, $V_{GS} = 20\text{V}$, $T_j = 175^\circ\text{C}$	—	20	32	$\text{m}\Omega$
Gate to Source Charge	Q_{gs}	$V_{DD} = 800\text{V}$, $I_D = 100\text{A}$	—	140	—	nC
Gate to Drain Charge	Q_{gd}	$V_{DD} = 800\text{V}$, $I_D = 100\text{A}$	—	220	—	nC
Total Gate Charge	Q_G	$V_{CC} = 800\text{V}$, $I_C = 100\text{A}$, $V_{GS} = -5/20\text{V}$	—	500	—	nC
Body Diode Forward Voltage	V_{SD}	$I_F = 50\text{A}$, $V_{GS} = -5\text{V}$	—	4.0	—	Volts
Input Capacitance	C_{iss}		—	10.2	—	nF
Output Capacitance	C_{oss}	$V_{GS} = 0$, $V_{DS} = 800\text{V}$, $f = 1\text{MHz}$	—	1.0	—	nF
Reverse Transfer Capacitance	C_{rss}		—	0.1	—	nF
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{DD} = 800\text{V}$, $I_D = 100\text{A}$,	—	17.2	—	ns
Rise Time	t_r	$V_{GS} = -2/20\text{V}$,	—	13.6	—	ns
Turn-off Delay Time	$t_{d(\text{off})}$	$R_G = 6.8\Omega$	—	62	—	ns
Fall Time	t_f	Inductive Load	—	35.6	—	ns

* Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.

**Total module leakage includes MOSFET leakage plus reverse Schottky diode leakage.

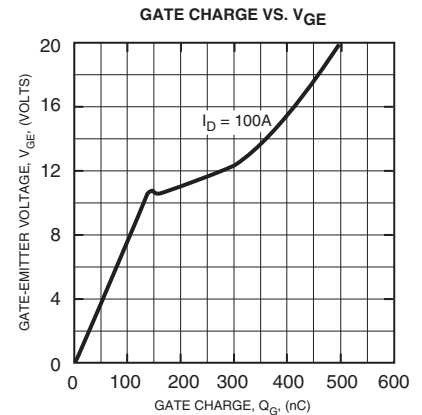
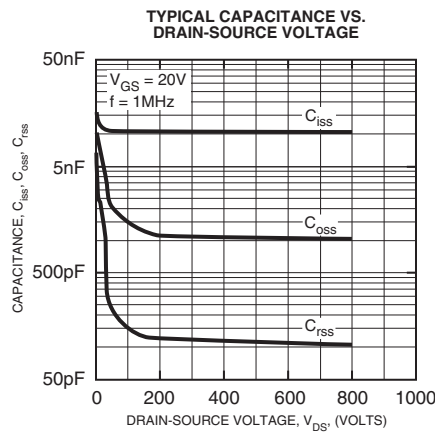
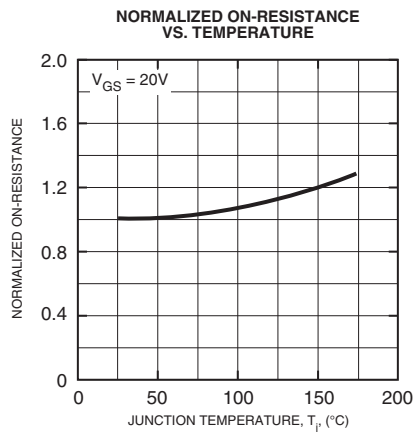
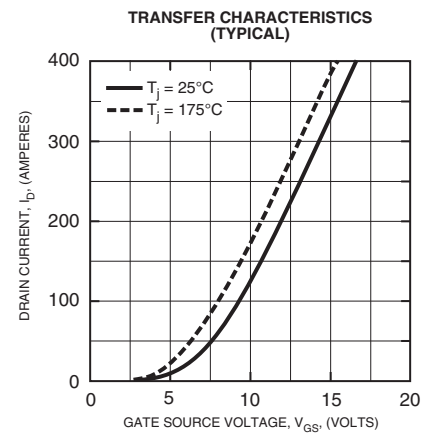
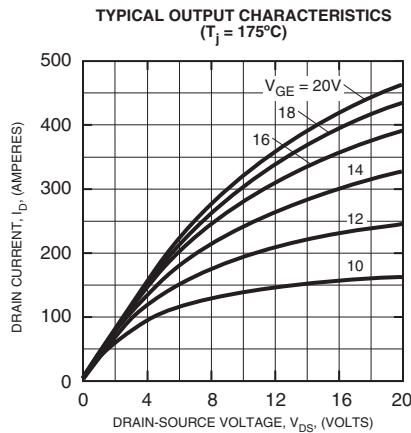
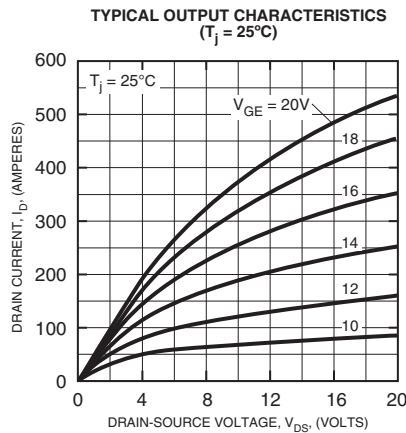
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Reverse Schottky Diode Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Diode Forward Voltage	V_{FM}	$I_F = 100\text{A}, V_{GS} = -5\text{V}$	—	1.6	2.0	Volts
		$I_F = 100\text{A}, V_{GS} = -5\text{V}, T_j = 175^\circ\text{C}$	—	2.5	3.2	Volts
Diode Capacitive Charge	Q_C	$V_R = 1200\text{V}, I_F = 100\text{A}, di/dt = 4000\text{A}/\mu\text{s}$	—	550	—	nC

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	MOSFET Part	—	—	0.167	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	Diode Part	—	—	0.294	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-s)}$	Per 1/2 Module, Thermal Grease Applied	—	0.04	—	$^\circ\text{C}/\text{W}$
Internal Inductance	L_{int}	MOSFET Part	—	10	—	nH



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